

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A flexible electronic device comprising: a flexible film; a substrate disposed on the flexible film, the substrate being different from the material of said flexible film and thickness of said substrate is larger than 0 μm and not larger than 200 μm ; and an electrically active thin film ~~layer~~-device; wherein an electrically active layer of the electrically active thin film device is disposed directly on the substrate.

2. (canceled).

3. (currently amended): The flexible electronic device according to claim 1, wherein said thin film ~~layer~~-device comprises a thin film transistor formed of a silicon thin film.

4. (original): The flexible electronic device according to claim 1, wherein said substrate is an insulating substrate.

5. (original): The flexible electronic device according to claim 4, wherein said insulating substrate is a glass substrate.

6. (original): The flexible electronic device according to claim 1, wherein said flexible film is an insulating film.

7. (original): The flexible electronic device according to claim 1, wherein said flexible film has a thermal conductivity higher than 0.01 W/cm·deg.

8.-26. (canceled).

27. (currently amended): A flexible electronic device comprising: a flexible film; a substrate disposed on the flexible film, the substrate being different from the material of said flexible film and thickness of said substrate is larger than 0 μm and not larger than 200 μm ; and a thin film device; wherein an electrically active layer of the electrically active thin film device is disposed directly on the substrate, and

wherein said thin film device is a thin film transistor formed of a silicon thin film.

28. (currently amended): A flexible electronic device comprising: a flexible film; a substrate disposed on the flexible film, the substrate being different from the material of said flexible film and thickness of said substrate is larger than 0 μm and not larger than 200 μm ; and a thin film device; wherein an electrically active layer of the electrically active thin film device is disposed directly on the substrate, and

wherein said flexible film has a thermal conductivity higher than 0.01 W/cm-deg.

29. (canceled).

30. (currently amended): A flexible electronic device comprising: a flexible film; a substrate disposed on the flexible film, the substrate being different from the material of said flexible film and thickness of said substrate is larger than 0 μm and not larger than 200 μm ; and a thin film device wherein an electrically active layer of the electrically active thin film device is disposed directly on the substrate, and wherein said flexible film has a thermal conductivity higher than 0.01 W/cm-deg.